



**NEC's HIGH NOISE REDUCTION
25 Mbps CMOS OUTPUT TYPE
8-PIN DIP OPTOCOUPLER**

**PS9661
PS9661L**

DESCRIPTION

NEC's PS9661 and PS9661L are optically coupled isolators containing a GaAlAs LED on the input side and a CMOS output IC on the output side.

These photocouplers are high common mode transient immunity (CMR), high-speed CMOS output type devices, making them ideal for high-speed logic interface circuits.

The PS9661 is in a plastic DIP (Dual In-line Package) and the PS9661L is lead bending type (Gull-wing) for surface mounting.

FEATURES

- High-speed response (25 Mbps)
- High common mode transient immunity ($CM_H, CM_L = \pm 20 \text{ kV}/\mu\text{s}$ TYP.)
- High isolation voltage ($BV = 3\,750 \text{ V r.m.s.}$)
- Pulse width distortion ($t_{PHL} - t_{PLH} = 3 \text{ ns}$ TYP.)
- Ordering number of tape product: PS9661L-E3, E4: 1 000 pcs/reel

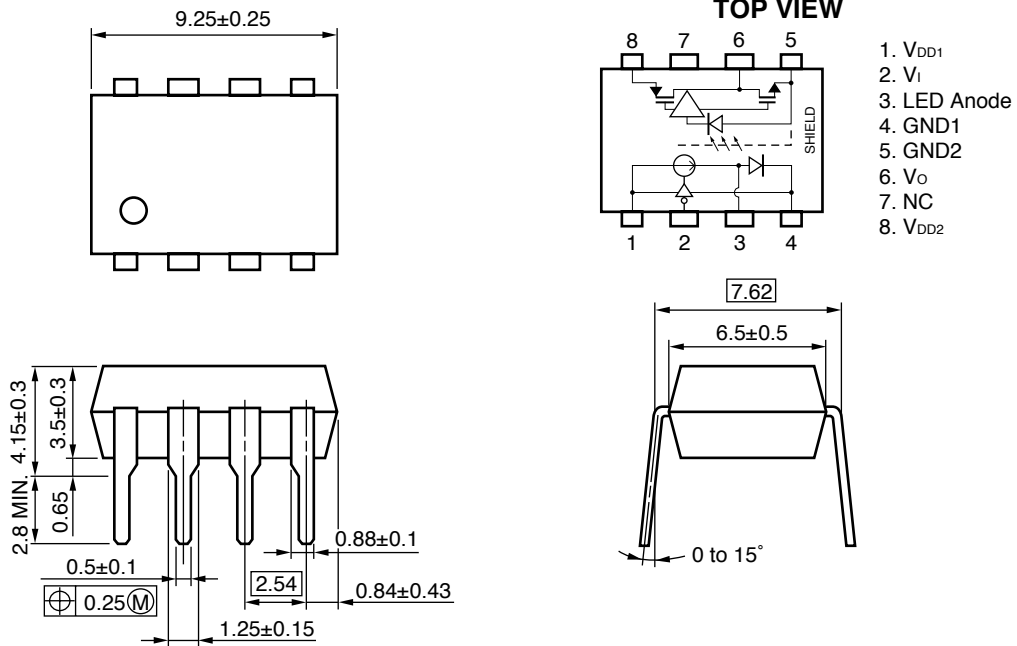
APPLICATIONS

- Factory Automation Network
- Measurement equipment
- PDP

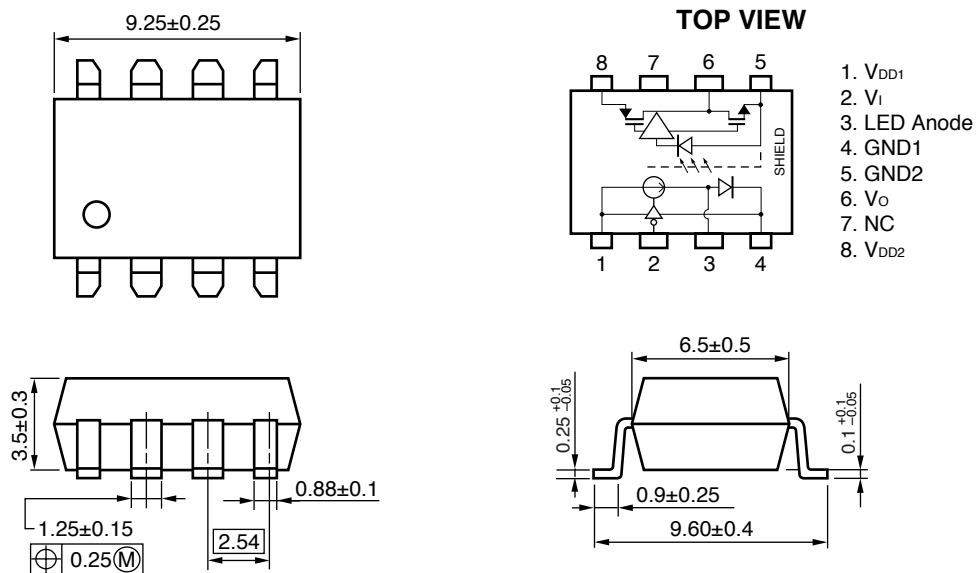
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PACKAGE DIMENSIONS (UNIT: mm)

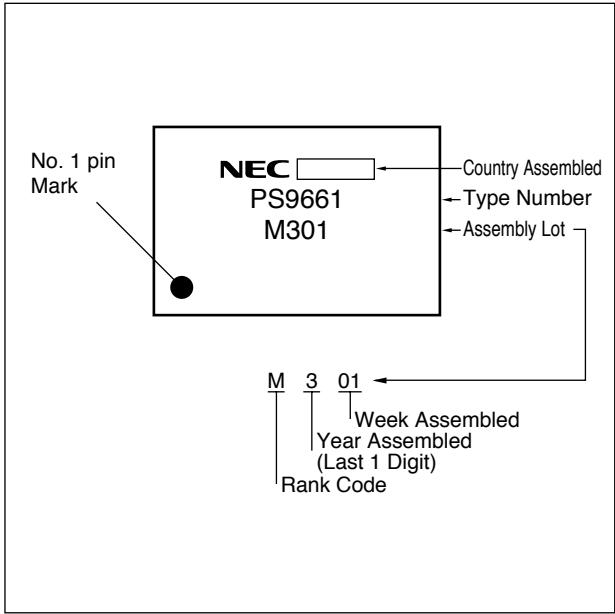
PS9661



PS9661L



MARKING EXAMPLE



ORDERING INFORMATION

Part Number	Package	Packing Style
PS9661	8-pin DIP	Magazine case 50 pcs
PS9661L		
PS9661L-E3		Embossed Tape 1 000 pcs/reel
PS9661L-E4		

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Input Voltage	V _I	−0.5 to V _{DD1} +0.5	V
Detector	Supply Voltage	V _{DD1} , V _{DD2}	0 to 5.5	V
	Output Voltage	V _O	−0.5 to V _{DD2} +0.5	V
	Output Current	I _O	10	mA
Isolation Voltage ^{*1}		BV	3 750	Vr.m.s.
Total Power Dissipation		P _T	150	mW
Operating Ambient Temperature		T _A	−40 to +85	°C
Storage Temperature		T _{stg}	−40 to +125	°C

^{*1} AC voltage for 1 minute at T_A = 25°C, RH = 60% between input and output.

RECOMMENDED OPERATING CONDITIONS (T_A = 25°C)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
High Level Input Voltage	V _{IH}	2.0		V _{DD1}	V
Low Level Input Voltage	V _{IL}	0		0.8	V
Supply Voltage	V _{DD1} , V _{DD2}	4.5	5.0	5.5	V
Rise Time	t _r			100	ns
Fall Time	t _f				

ELECTRICAL CHARACTERISTICS (Recommended Operating Conditions Unless Otherwise Specified. Note That $V_{DD1} = V_{DD2} = 5\text{ V}$.)

Parameter		Symbol	Conditions	MIN.	TYP.*1	MAX.	Unit	Fig.
Diode	Low Level Supply Current	I_{DD1L}	$V_I = 0\text{ V}$		7.5	10.0	mA	1
	High Level Supply Current	I_{DD1H}	$V_I = V_{DD1}$		0.15	3.0		2
	Input Current	I_I	$V_I = 0\text{ V}$ or $V_I = V_{DD1}$	-10		10	μA	3, 4
Detector	Output Supply Current	I_{DD2H}	$V_I = V_{DD1}$		7	9	mA	5
		I_{DD2L}	$V_I = 0\text{ V}$		5	9		6
	High Level Output Voltage	V_{OH}	$I_O = -20\text{ }\mu\text{A}$, $V_I = V_{IH}$	4.4	5.0		V	7
			$I_O = -4\text{ mA}$, $V_I = V_{IH}$	4.0	4.8			
	Low Level Output Voltage	V_{OL}	$I_O = 20\text{ }\mu\text{A}$, $V_I = V_{IL}$		0.01	0.1		8
			$I_O = 4\text{ mA}$, $V_I = V_{IL}$		0.32	1.0		
Coupled	Isolation Resistance	R_{I-O}	$V_{I-O} = 1\text{ kV}_{DC}$, $R_H = 40\text{ to }60\%$, $T_A = 25^\circ\text{C}$	10^{11}			Ω	
	Isolation Capacitance	C_{I-O}	$V = 0\text{ V}$, $f = 1\text{ MHz}$, $T_A = 25^\circ\text{C}$		1.3		pF	
	Propagation Delay Time (H $\rightarrow$ L)	t_{PHL}	$C_L = 15\text{ pF}$, CMOS Signal Levels		20	40	ns	9
	Propagation Delay Time (L $\rightarrow$ H)	t_{PLH}			23	40		
	Pulse Width	PW		40				
	Pulse Width Distortion (PWD)	$ t_{PHL} - t_{PLH} $			3	8		
	Propagation Delay Skew	t_{PSK}				20		
	Rise Time	t_r			9			
	Fall Time	t_f			8			
	Common Mode Transient Immunity at High Level Output	CM_H	$V_I = V_{DD1} = V_{DD2} = 5\text{ V}$, $V_O > 0.8\text{ }V_{DD1}$, $V_{CM} = 1\text{ kV}$, $T_A = 25^\circ\text{C}$	10	20		kV/ μs	10
	Common Mode Transient Immunity at Low Level Output	CM_L	$V_I = V_{DD1} = V_{DD2} = 5\text{ V}$, $V_I = 0\text{ V}$ $V_O < 0.8\text{ }V_{DD1}$, $V_{CM} = 1\text{ kV}$	10	20			

*1 Typical values at $T_A = 25^\circ\text{C}$

USAGE CAUTIONS

1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
2. By-pass capacitor of more than 0.1 μF is used between V_{DD} and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.

MEASUREMENT CIRCUITS FOR ELECTRICAL CHARACTERISTICS

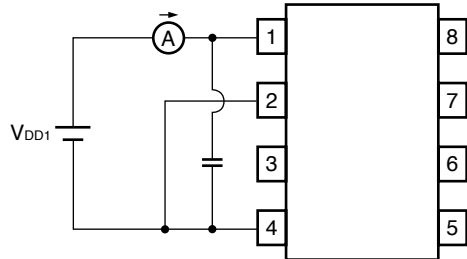
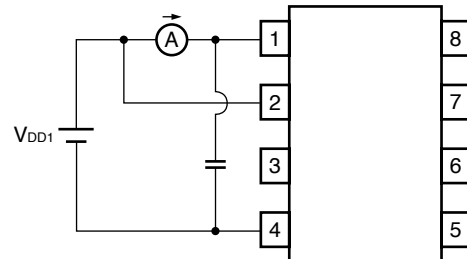
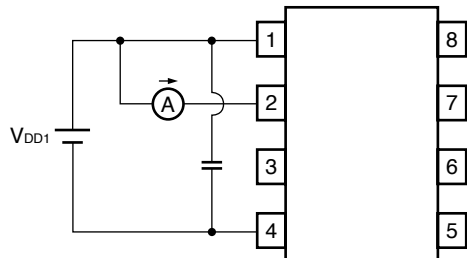
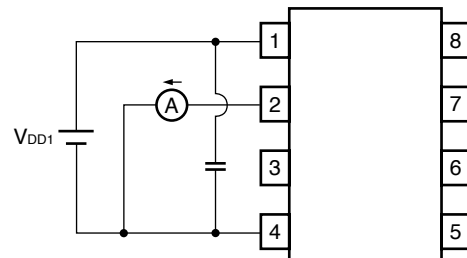
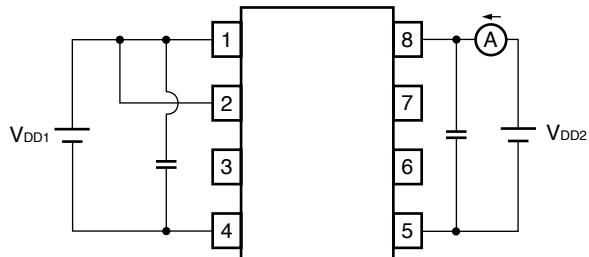
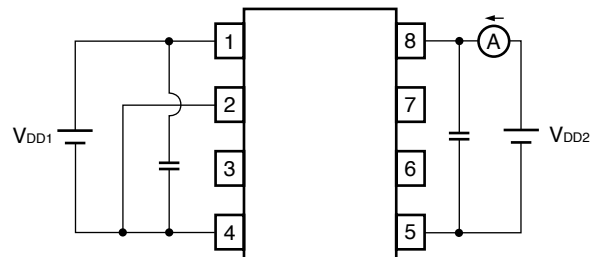
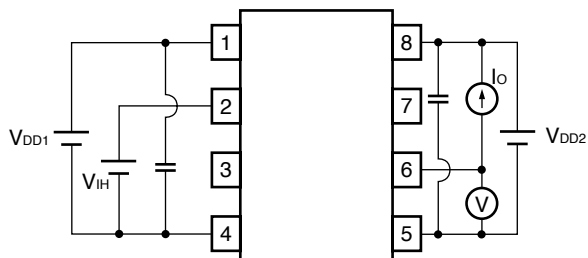
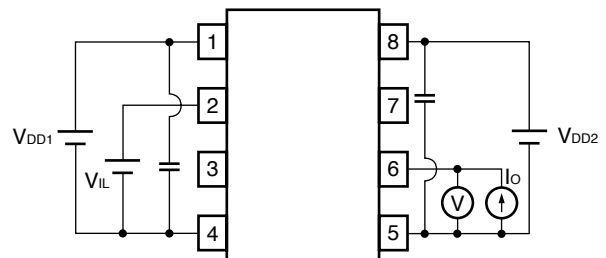
Fig. 1 I_{DD1L} Fig. 2 I_{DD1H} Fig. 3 I_{IH} Fig. 4 I_{IL} Fig. 5 I_{DD2H} Fig. 6 I_{DD2L} Fig. 7 V_{OH} Fig. 8 V_{OL} 

Fig. 9 t_{PHL}/t_{PLH}

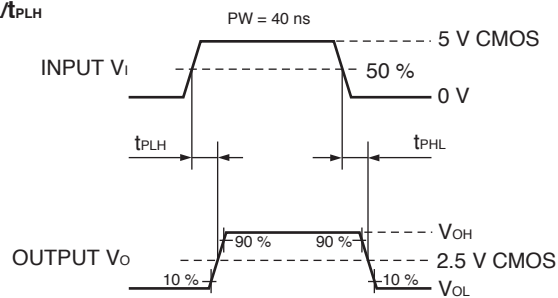
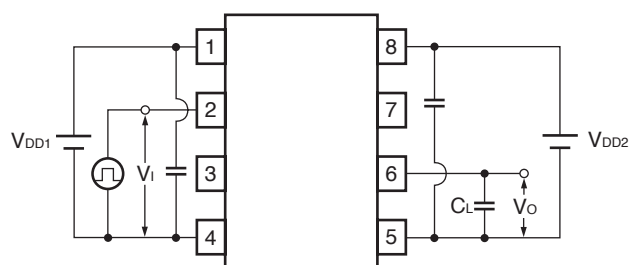
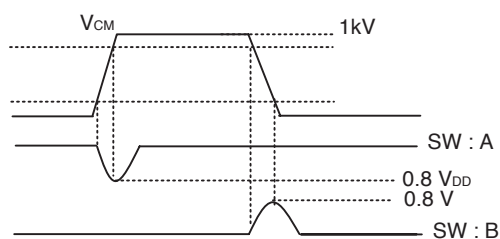
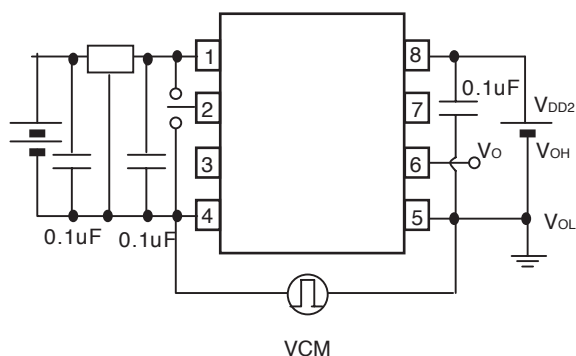


Fig. 10 C_{MH}/C_{ML}



Life Support Applications

These NEC products are not intended for use in life support devices, appliances, or systems where the malfunction of these products can reasonably be expected to result in personal injury. The customers of CEL using or selling these products for use in such applications do so at their own risk and agree to fully indemnify CEL for all damages resulting from such improper use or sale.

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